

SPIN-CURRENT SWITCHED MAGNETIC MEMORY ELEMENT  
SUITABLE FOR CIRCUIT INTEGRATION AND METHOD  
OF FABRICATING THE MEMORY ELEMENT

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**ABSTRACT**

10        A magnetic memory element switchable by current injection includes a plurality of magnetic layers, at least one of the plurality of magnetic layers having a perpendicular magnetic anisotropy component and including a current-switchable magnetic moment, and at least one barrier layer formed adjacent to the plurality of magnetic layers (e.g., between two of the magnetic layers). The memory element has the switching threshold current and device  
15      impedance suitable for integration with complementary metal oxide semiconductor (CMOS) integrated circuits.

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